

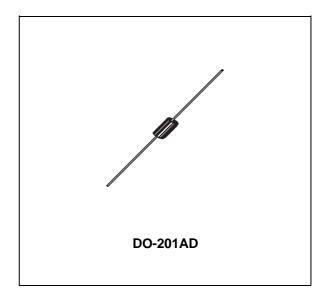
LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

I _{F(AV)}	3 A
V _{RRM}	40 V
T j	150℃
V _F (max)	0.475 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP



DESCRIPTION

Axial Power Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters. Packaged in DO-201AD these devices are intended for use in low voltage, high frequency inverters, free wheeling, polarity protection and small battery chargers.

ABSOLUTE RATINGS (limiting values)

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Symbol	Parameter	1N5820	1N5821	1N5822	Unit	
V _{RRM}	Repetitive peak reverse voltage	20	30	40	V	
I _{F(RMS)}	RMS forward current	10			Α	
I _{F(AV)}	Average forward current	$T_L = 100^{\circ}C$ $\delta = 0.5$			3	Α
		$T_L = 110^{\circ}C$ $\delta = 0.5$	3	3		Α
I _{FSM}	Surge non repetitive forward current		80		Α	
T _{stg}	Storage temperature range	- 65 to + 150			°C	
Tj	Maximum operating junction temperature *			150		
dV/dt	Critical rate of rise of reverse voltage			10000		

^{* :} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ thermal runaway condition for a diode on its own heatsink

July 1999 - Ed: 2A

THERMAL RESISTANCES

Symbol	Paramete	Value	Unit	
R _{th (j-a)}	Junction to ambient	Lead length = 10 mm	80	°C/W
R _{th (j-l)}	Junction to lead	Lead length = 10 mm	25	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Co	1N5820	1N5821	1N5822	Unit	
I _R *	Reverse leakage	Tj = 25°C	$V_R = V_{RRM}$	2	2	2	mA
	current	Tj = 100°C		20	20	20	mA
V _F *	Forward voltage drop	Tj = 25°C	IF = 3 A	0.475	0.5	0.525	V
		Tj = 25°C	I _F = 9.4 A	0.85	0.9	0.95	V

Pulse test : * tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equations :

 $P = 0.33 \times I_{F(AV)} + 0.035 I_{F}^{2}_{(RMS)} \text{ for } 1N5820 / 1N5821$ $P = 0.33 \times I_{F(AV)} + 0.060 I_{F}^{2}_{(RMS)} \text{ for } 1N5822$

Fig. 1: Average forward power dissipation versus average forward current (1N5820/1N5821).

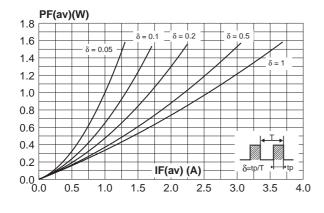


Fig. 2: Average forward power dissipation versus average forward current (1N5822).

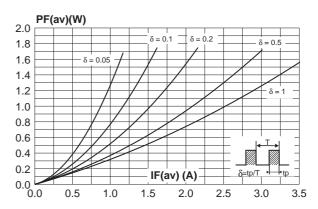


Fig. 2-1: Average forward current versus ambient temperature (δ =0.5) (1N5820/1N5821).

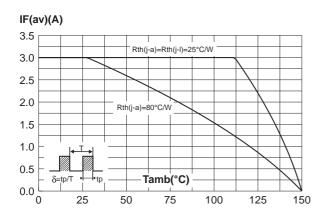


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values) (1N5820/1N5821).

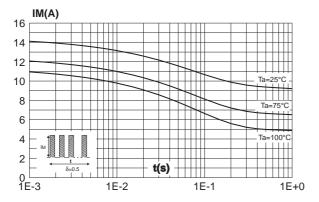


Fig. 4: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35mm, recommended pad layout).

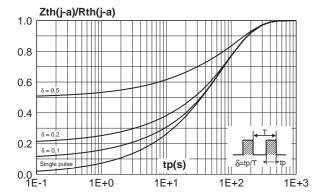


Fig. 2-2: Average forward current versus ambient temperature (δ =0.5) (1N5822).

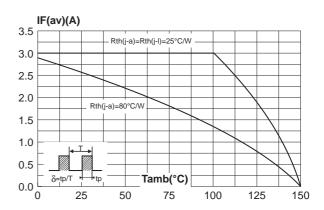


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values) (1N5822).

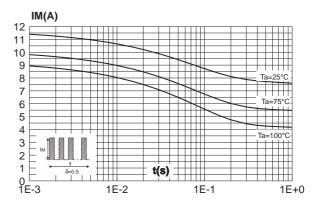
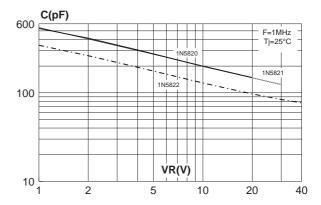


Fig. 5: Junction capacitance versus reverse voltage applied (typical values).



57

Fig. 6-1: Reverse leakage current versus reverse voltage applied (typical values) (1N5820/1N5821).

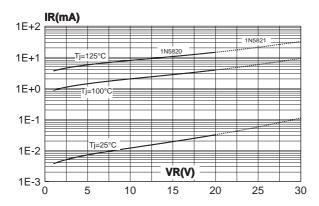


Fig. 6-2: Reverse leakage current versus reverse voltage applied (typical values) (1N5822).

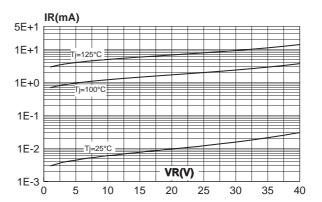


Fig. 7-1: Forward voltage drop versus forward current (typical values) (1N5820/1N5821).

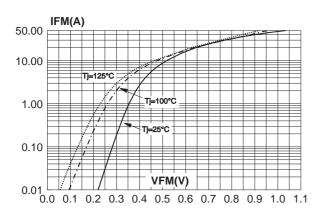


Fig. 7-2: Forward voltage drop versus forward current (typical values) (1N5822).

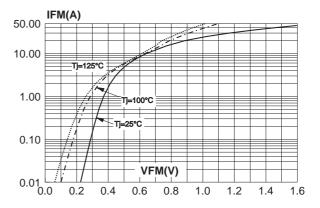
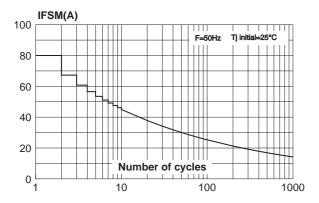


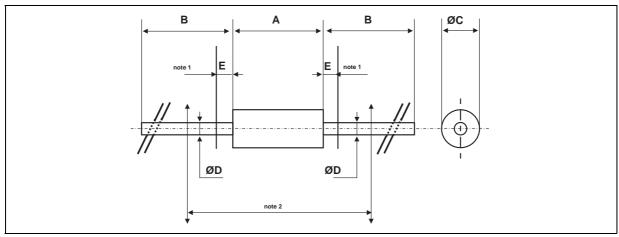
Fig. 8: Non repetitive surge peak forward current versus number of cycles.



4/5

PACKAGE MECHANICAL DATA

DO-201AD plastic



	DIMENSIONS				NOTES		
REF. Millimeters		neters	Inches				
	Min.	Max.	Min.	Max.			
Α		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E		
В	25.40		1.000				
ØC		5.30		0.209	2 - The minimum axial length within which the device may be		
ØD		1.30		0.051	placed with its leads bent at right angles is 0.59"(15 mm)		
Е		1.25		0.049			

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
1N582x	Part number cathode ring	DO-201AD	1.12g	600	Ammopack
1N582xRL	Part number cathode ring	DO-201AD	1.12g	1900	Tape & reel

■ Epoxy meets UL94,V0

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